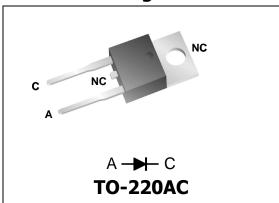


# **LQA05TC600 Qspeed**<sup>™</sup> Family 600 V, 5 A Q-Series PFC Diode

## **Product Summary**

$I_{F(AVG)}$	5	Α
$V_{RRM}$	600	V
Q <sub>RR</sub> (Typ at 125 °C)	27	nC
I <sub>RRM</sub> (Typ at 125 °C)	1.65	Α
Softness t <sub>b</sub> /t <sub>a</sub> (Typ at 125 °C)	1.4	

## **Pin Assignment**



## **RoHS Compliant**

Package uses Lead-free plating and Green mold compound. Halogen free per IEC 61249-2-21.

## **General Description**

This device has the lowest  $Q_{RR}$  of any 600 V silicon diode. Its recovery characteristics increase efficiency, reduce EMI and eliminate snubbers.

## **Applications**

- Power Factor Correction (PFC) boost diode
- · Motor drive circuits
- DC-AC inverters

### **Features**

- Low Q<sub>RR</sub>, low I<sub>RRM</sub>, low t<sub>RR</sub>
- High dI<sub>F</sub>/dt capable (1000 A / μs)
- Soft recovery

### **Benefits**

- · Increases efficiency
  - Eliminates need for snubber circuits
  - Reduces EMI filter component size & count
- Enables extremely fast switching

## **Absolute Maximum Ratings**

Absolute maximum ratings are the values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Symbol	Parameter	Conditions	Rating	Units
$V_{RRM}$	Peak repetitive reverse voltage		600	V
I <sub>F(AVG)</sub>	Average forward current	$T_{\rm J} = 150$ °C, $T_{\rm C} = 115$ °C	5	Α
$I_{FSM}$	Non-repetitive peak surge current	60 Hz, 1/2 cycle	50	Α
$I_{FSM}$	Non-repetitive peak surge current	$1/2$ cycle of t = 28 $\mu$ s Sinusoid, $T_C$ = 25 °C	350	Α
$T_{J(MAX)}$	Maximum junction temperature		150	°C
$T_{STG}$	Storage temperature		-55 to 150	°C
	Lead soldering temperature	Leads at 1.6 mm from case, 10 sec	300	°C
$V_{ISOL}$	Isolation voltage (leads-to-tab)	DC, + to tab	2500	V
$P_D$	Power dissipation	T <sub>C</sub> = 25 °C	43.1	W

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## LOA05TC600

## **Thermal Resistance**

Symbol	Resistance from:	Conditions	Rating	Units
$R_{\theta JA}$	Junction to ambient	TO-220	62	°C/W
$R_{\theta JC}$	Junction to case	TO-220	2.9	°C/W

Electrical Specifications at T<sub>J</sub> = 25 °C (unless otherwise specified)

Symbol	Parameter	Condition		Min	Тур	Max	Units
DC Chara	DC Characteristics						
т	Dovorco current	$V_R = 600 \text{ V}, T_J = 25 \text{ °C}$		-	-	15	μΑ
$I_{R}$	Reverse current	$V_R = 600 \text{ V}, T_J = 125 \text{ °}$	C.	-	0.4	-	mA
$V_{F}$	Forward voltage	$I_F = 5 \text{ A, } T_J = 25 \text{ °C}$		-	2.825	3.14	٧
<b>v</b> <sub>F</sub>	Forward voitage	$I_F = 5 \text{ A, } T_J = 150 ^{\circ}\text{C}$		-	2.28	1	٧
$C_{J}$	Junction capacitance	V <sub>R</sub> = 10 V, 1 MHz		-	21	1	pF
Dynamic	Characteristics						
+	Reverse recovery time	dI/dt = 200 A/μs	T <sub>J</sub> = 25 °C	-	11	15	ns
$t_RR$	Reverse recovery time	$V_R = 400 \text{ V}, I_F = 5 \text{ A}$	T <sub>J</sub> = 125 °C	-	24	-	ns
0	Reverse recovery charge	dI/dt = 200 A/μs	T <sub>J</sub> = 25 °C	-	6	10	nC
$Q_{RR}$	Reverse recovery charge	$V_R = 400 \text{ V}, I_F = 5 \text{ A}$	T <sub>J</sub> =125 °C	-	27	-	nC
т	Maximum reverse recovery	dI/dt = 200 A/μs	$T_J = 25$ °C	-	0.95	1.3	Α
$I_{RRM}$	current	$V_R = 400 \text{ V, } I_F = 5 \text{ A}$	T <sub>J</sub> = 125 °C	-	1.65	-	Α
	Softness factor = $\frac{t_B}{t_B}$	dI/dt = 200 A/μs	T <sub>J</sub> = 25 °C	-	1	-	
S	Sortness factor = $\frac{1}{t_A}$ $V_R = 400 \text{ V, } I_F = 5 \text{ A}$	T <sub>J</sub> = 125 °C	-	1.4	-		

**Note to component engineers**: Q-Series diodes employ Schottky technologies in their design and construction. Therefore, Component Engineers should plan their test setups to be similar to those for traditional Schottky test setups. (For additional details, see Application Note AN-300.)

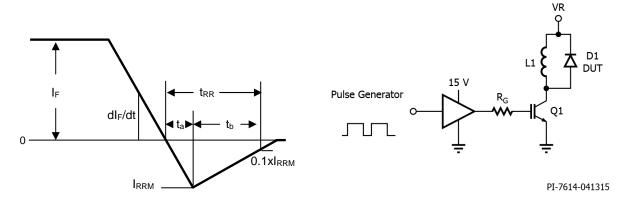
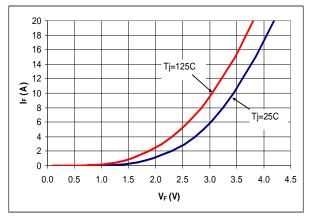


Figure 1. Reverse Recovery Definitions.

Figure 2. Reverse Recovery Test Circuit.

## Electrical Specifications at $T_1 = 25$ °C (unless otherwise specified)

60



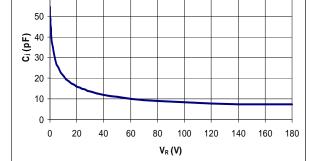
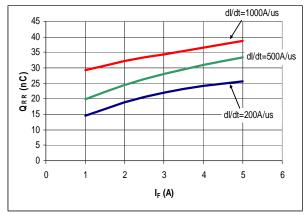


Figure 3. Typical I<sub>F</sub> vs. V<sub>F</sub>.

Figure 4. Typical C<sub>J</sub> vs. V<sub>R</sub>.



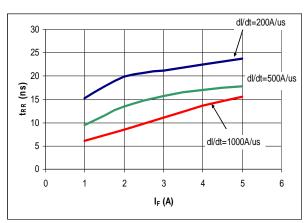
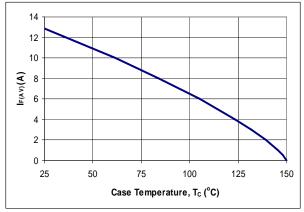


Figure 5. Typical  $Q_{RR}$  vs.  $I_F$  at  $T_J = 125$  °C.

Figure 6. Typical  $t_{RR}$  vs.  $I_F$  at  $T_J$  = 125 °C.



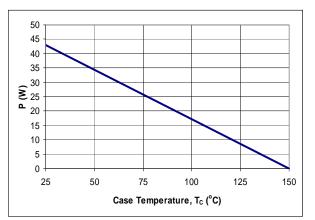


Figure 7. DC Current Derating Curve.

Figure 8. Power Derating Curve.

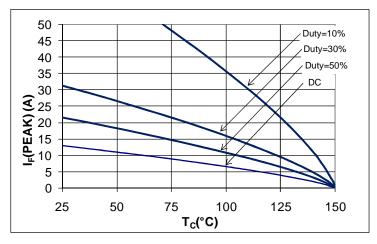


Figure 9.  $I_F$  (PEAK) vs.  $T_{C_f}$  f = 70 kHz.

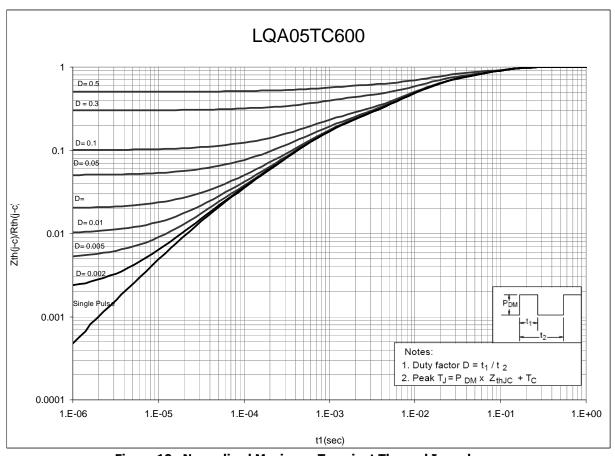
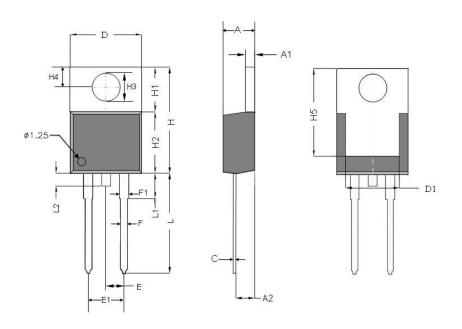


Figure 10. Normalized Maximum Transient Thermal Impedance.

## **Dimensional Outline Drawings**



	Millimeters		
Dim	MIN MAX		
Α	4.32	4.57	
<b>A1</b>	1.14	1.40	
A2	2.59	2.74	
С	0.37	0.44	
D	10.13	10.24	
D1	7.57	7.68	
E	2.49	2.59	
E1	5.03	5.13	
F	0.787	1.00	
F1	1.23	1.36	
Н	14.71	15.31	
H1	6.20	6.55	
H2	8.51	8.76	
Н3	3.71	3.96	
Н4	2.54	2.79	
Н5	12.34	12.45	
L	13.72	14.22	
L1	-	6.36	
L2	1.27	1.78	

TO-220AC package conforms to JEDEC outline TO-220AC

Mechanical Mounting Method	ethod Maximum Torque / Pressure specification		
Screw through hole in package tab	1 Newton Meter (nm) or 8.8 inch-pounds (lb-in)		
Clamp against package body 12.3 kilogram-force per square centimeter (kgf/cm²) or 175			

**Soldering time and temperature:** This product has been designed for use with high-temperature, lead-free solder. The component leads can be subjected to a maximum temperature of 300 °C, for up to 10 seconds. See Application Note AN-303, for more details.

## **Ordering Information**

Part Number	Package	Packing
LQA05TC600	TO-220AC	50 units/tube

The information contained in this document is subject to change without notice.

# LQA05TC600

Revision	vision Notes	
1.8 Released by Qspeed		05/09
1.9 Converted to Power Integrations Document		01/11
2.0 Updated with new Brand Style.		11/15



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